

# HN58C256 Series — Under Development

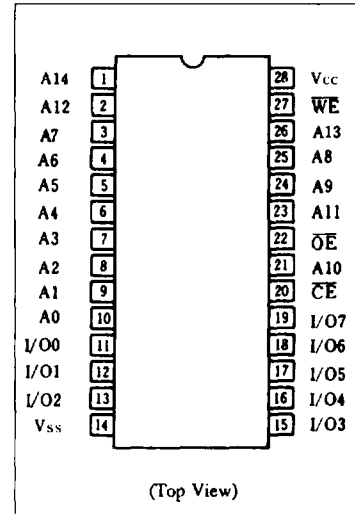
32768-Word × 8-Bit Electrically Erasable and Programmable CMOS ROM

The Hitachi HN58C256 is an electrically erasable and programmable ROM organized as 32768-word x 8-bit. It realizes high speed, low power consumption, and a high reliability, employing advanced MNOS memory technology and CMOS process and circuitry technology. It also has a 64-byte page reprogramming function to make its erase and write operations faster.

## Features

- Single 5 V supply
- On-chip latches: address, data,  $\overline{CE}$ ,  $\overline{OE}$ ,  $\overline{WE}$
- Automatic byte write: 10 ms max
- Automatic page write (64 bytes): 10 ms max
- Fast access time: 150 ns max / 200 ns max
- Low power dissipation: 20 mW/MHz, typ (Active)  
100  $\mu$ W max (Standby)
- $\overline{Data}$  polling
- Data protection circuit on power on/off
- Conforms to JEDEC byte-wide standard
- Reliable CMOS with MNOS cell technology
- $10^5$  erase/write cycles (in page mode) and 10 year data retention

## Pin Arrangement



## Ordering Information

Type No.	Access Time	Package
HN58C256P-15	150 ns	600-mil 28-pin
HN58C256P-20	200 ns	plastic DIP (DP-28)
HN58C256FP-15	150 ns	28-pin
HN58C256FP-20	200 ns	plastic SOP*1 (FP-28D/DA)

Notes: \*1. T is added to the end of the type no. for an SOP of 3.00 mm (max) thickness.

Die shipment is also available. Because the die has a  $\overline{RES}$  pad, it can perform a reset function (refer to HN58C66 data sheet).

## Pin Description

Pin Name	Function
A0–A14	Address
I/O0–I/O7	Input/Output
$\overline{OE}$	Output enable
$\overline{CE}$	Chip enable
$\overline{WE}$	Write enable
Vcc	Power supply
Vss	Ground

The specifications of this device are subject to change without notice. Please contact your nearest Hitachi's Sales Dept. regarding specifications.



Block Diagram

